



IS281GB (Compact Range)

DESCRIPTION

The IS281GB is an optically coupled isolator consisting of an infrared light emitting diode and an NPN silicon photo transistor. It belongs to Isocom's Compact range of opto-couplers

FEATURES

- Low profile package (half pitch)
- AC Isolation test voltage $3750V_{RMS}$
- Low coupling capacitance typically 0.3pF
- CTR selections available
- Wide temperature range
- Lead free
- Halogen Free

APPLICATIONS

- Power Supply Feedback Voltage/Current
- Industrial system controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedance

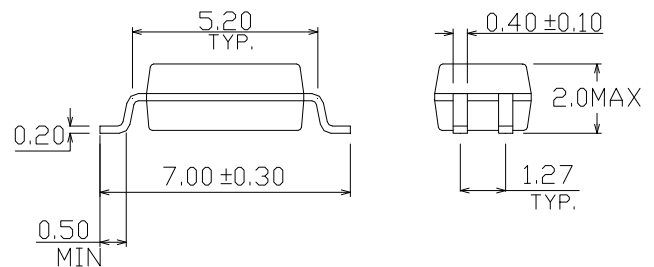
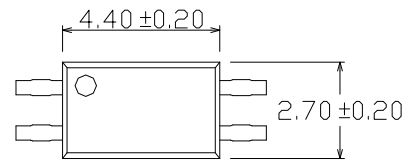
ORDER INFORMATION

- Available in Tape and Reel with 1000 & 5000 pieces per reel

MARKING INFORMATION

Please note that the device will be marked with the generic part number "THP*" the date code will also be marked on the device.

* Denotes internal binning identification



ABSOLUTE MAXIMUM RATINGS

Input Diode

Forward Current	60mA
Reverse Voltage	6V
Power dissipation	70mW
Derating Factor > 90°C	2mW / °C

Output Transistor

Collector to Emitter Voltage	80V
Emitter to Collector Voltage	7V
Collector Current	50mA
Power Dissipation	150mW
Derating Factor > 70°C	3.1mW / °C

Total Package

Isolation test Voltage	3750V _{RMS}
Operating Temperature	-55 to 110 C
Storage Temperature	-55 to 150 C

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ELECTRICAL CHARACTERISTICS

Ambient Temperature = 25°C unless otherwise specified

INPUT

Parameter	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$		1.20	1.40	V
Reverse Leakage	I_R	$V_R = 4\text{V}$			10	μA
Input Capacitance	C_{in}	$V = 0\text{V}, f = 1 \text{ KHz}$		30	250	pF

OUTPUT

Parameter	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector—Emitter breakdown Voltage	BV_{CEO}	$I_C = 100\mu\text{A}$	80			V
Emitter—Collector breakdown Voltage	BV_{ECO}	$I_E = 100\mu\text{A}$	7			V
Collector dark Current	I_{CEO}	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$			100	nA

COUPLED

Parameter	Symbol	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	CTR	$I_F = 10\text{mA}, V_{CE} = 5\text{V}$	100		600	%
Collector—Emitter saturation Voltage	V_{CEsat}	$I_F = 10\text{mA}, I_C = 1\text{mA}$		0.1	0.2	V
Input to output isolation Voltage	V_{ISO}	See note 1	3750			V_{RMS}
Output rise time	t_r	$V_{ce} = 2\text{V}, I_c = 2\text{mA}, R_L = 100\Omega$		5.0	18	μS
Output fall time	t_f	$V_{ce} = 2\text{V}, I_c = 2\text{mA}, R_L = 100\Omega$		3.0	18	μS
Cut off frequency	f_c	$I_F = 10\text{mA}, V_{CE} = 5\text{V}, R_L = 100\Omega$		100		kHz
Coupling Capacitance	C_k	$f = 1 \text{ MHz}$		0.3		pF

Note 1 Measured with input leads shorted together and output leads shorted together



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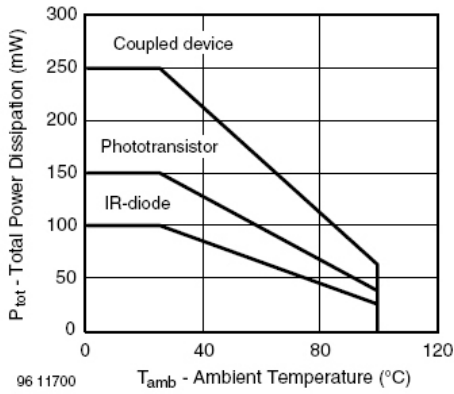


Figure 4. Total Power Dissipation vs. Ambient Temperature

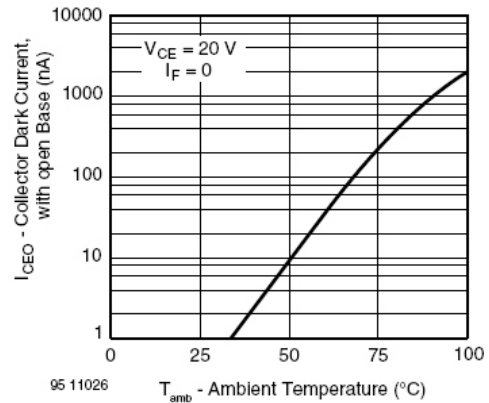


Figure 7. Collector Dark Current vs. Ambient Temperature

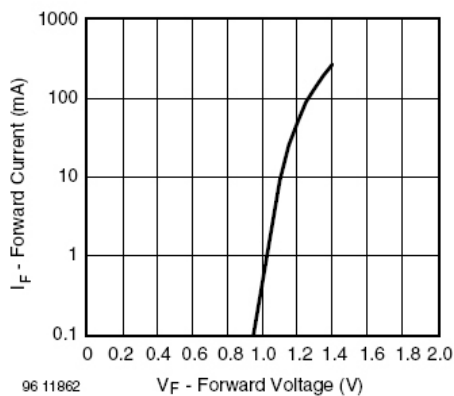


Figure 5. Forward Current vs. Forward Voltage

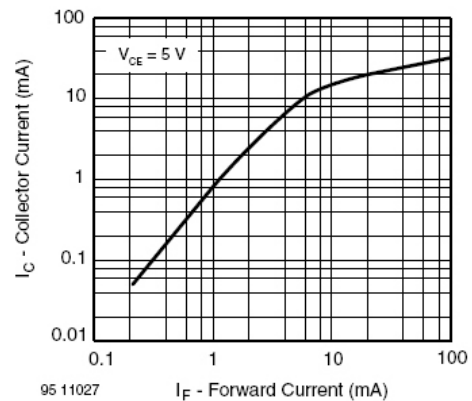


Figure 8. Collector Current vs. Forward Current

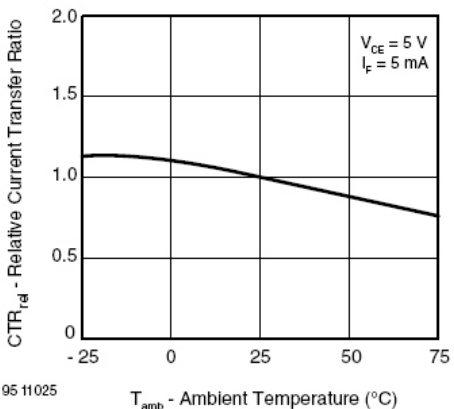


Figure 6. Relative Current Transfer Ratio vs. Ambient Temperature

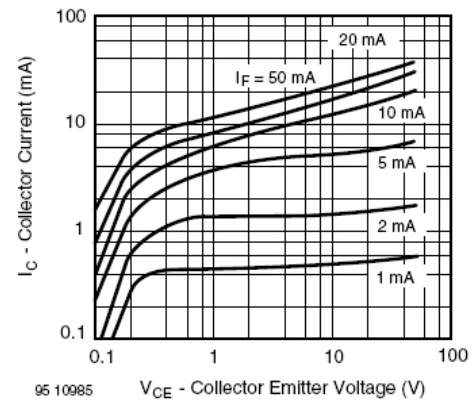


Figure 9. Collector Current vs. Collector Emitter Voltage



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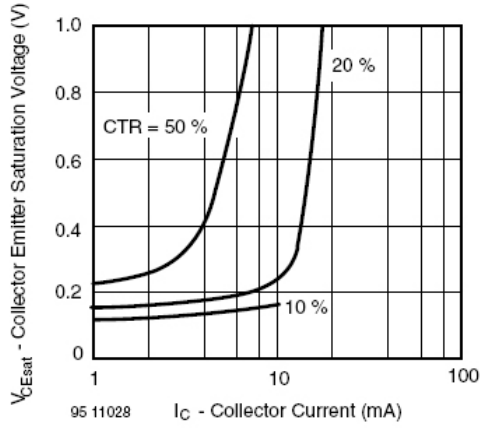


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

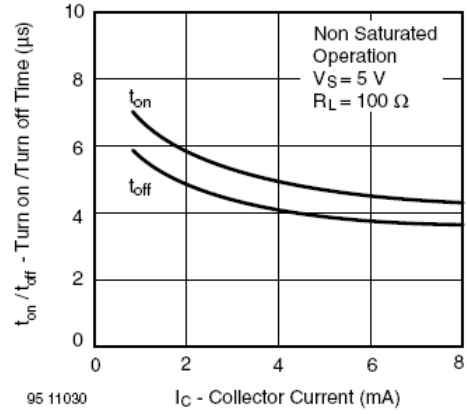


Figure 13. Turn on/off Time vs. Collector Current

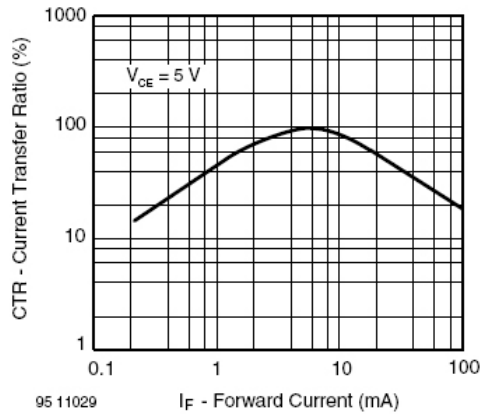


Figure 11. Current Transfer Ratio vs. Forward Current

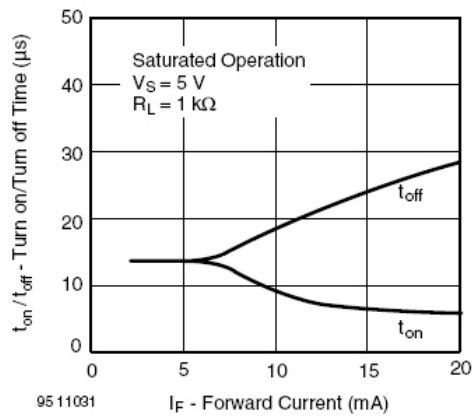


Figure 12. Turn on/off Time vs. Forward Current